



AMP5047P

SOLID STATE HIGH POWER PULSE AMPLIFIER

FEATURES

Class AB GaN Devices
 Designed for X-Band high power Pulse applications
 Built-in protection circuits
 High reliability and ruggedness

ELECTRICAL SPECIFICATIONS

Parameter	Specification			Notes
Operating Frequency ¹	9.7 - 9.9 GHz			
Peak Pulse Output Power	1000 Watt Min			Peak Pulse
Peak Power Gain ¹	60 dB Min			Lower gain, phase & gain matching for combining is available
Input Pulse Characteristics	Pulse Width(tp)	Duty Cycle(δ)	PRF	Nominal values
	0.1 - 50 μS	5 %	10 KHz	
Pulse Rise / Fall Time	50 nS Max			
Pulse Droop	0.5 dB Max			With 50 μS
Input Return Loss	12 dB Min			Relative to 50 Ohm
Harmonics	-30 dBc Nom			
Spurious	-60 dBc Max			Non-harmonics or Gaussian
Operating Voltage	42 VDC Nom			
Current Consumption	4 Amp Avg. Typ			With 5% duty cycle
Load VSWR	∞ : 1			External output Isolator required

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Note
Operating Case Temperature	-20 to +70°C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	180 x 260 x 42 mm	Excluding Heatsink
Weight	TBD	
RF Connectors In/Out	SMA female / Type N female	WR-90 optional
DC Power / Interface Connector	7-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

Notes:

1 To combine 2 or more modules, specify lower gain, phase and gain matching when ordering.

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D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	
2	Pulse Gating Control	TTL
3	CURRENT SENSOR	$I_D @ 50mV/100mA$ Typ
4	TEMP SENSOR	$V_T @ 10mV/^\circ C + 500mV$ Typ
5	SHUTDOWN	TTL "Hi" = Disable Function @ 50mS (Option: 5uS Trigger/Pulse Modulator)
A1	VDD	42VDC
A2	GND	Ground

OUTLINE DRAWING

